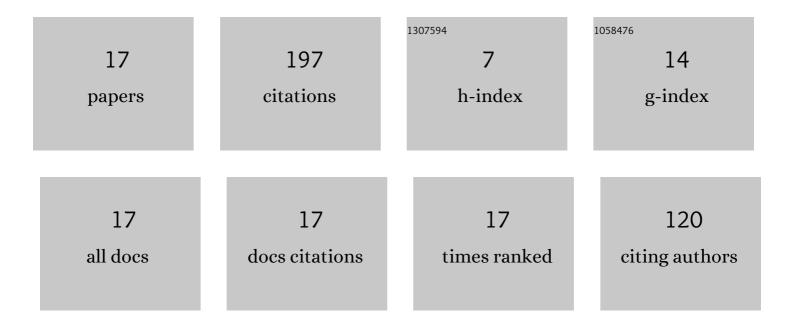
Shiji Fan

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Variations of composition and dielectric properties of Pb(In1/2Nb1/2)O3-Pb(Mg1/3Nb2/3)O3-PbTiO3 single crystal along growth direction. Journal of Applied Physics, 2013, 113, 124105.	2.5	32
2	Enhanced dielectric and piezoelectric properties in the [001]-poled 0.25Pb(In1/2Nb1/2)O3-0.43Pb(Mg1/3Nb2/3)O3-0.32PbTiO3 single crystal near morphotropic phase boundary by alternating current treatment. Journal of Applied Physics, 2020, 127, .	2.5	31
3	Growth of the Relaxor Based Ferroelectric Single Crystals Pb(In _{1/2} Nb _{1/2})O ₃ - Pb(Mg _{1/3} Nb _{2/3})O ₃ -PbTiO ₃ by Vertical Bridgman Technique, Ferroelectrics, 2010, 401, 173-180.	0.6	26
4	Composition and electrical properties characterization of a 5―diameter PIN-PMN-PT single crystal by the modified Bridgman method. Journal of Alloys and Compounds, 2021, 851, 156145.	5.5	24
5	High composition uniformity of 4″ of PIN-PMN-PT single crystals grown by the modified Bridgman method. Journal of Crystal Growth, 2017, 468, 331-334.	1.5	21
6	Compositional segregation and electrical properties characterization of [001]- and [011]-oriented co-growth Pb(In1/2Nb1/2)O3-Pb(Mg1/3Nb2/3)O3-PbTiO3 single crystal. Journal of Applied Physics, 2018, 123, 154107.	2.5	19
7	GaN crystals growth in the Na-Li-Ca flux by liquid phase epitaxy (LPE) technique. Journal of Crystal Growth, 2019, 521, 30-33.	1.5	9
8	Growth of GaN Crystals by the Na Flux Method Under a Temperature Gradient. Journal of Electronic Materials, 2014, 43, 1219-1225.	2.2	7
9	Fabrication of GaN single crystals at 700°C using Na-Li-Ca mixed flux system. AIP Advances, 2018, 8, .	1.3	6
10	Growth Temperature Dependence of Morphology of GaN Single Crystals in the Na-Li-Ca Flux Method. Journal of Electronic Materials, 2018, 47, 1569-1574.	2.2	6
11	Growth and electrical properties characterization of Pb(In1/2Nb1/2)O3–PbTiO3 tetragonal single crystal by the modified flux-Bridgman method. Journal of Crystal Growth, 2017, 468, 382-386.	1.5	4
12	Effects of Growth Temperature on Morphology of GaN Crystals by Na Flux Liquid Phase Epitaxial Method. Journal of Electronic Materials, 2019, 48, 3570-3578.	2.2	3
13	Effects of Cooling Process on GaN Crystal Growth by Na Flux Method. Journal of Electronic Materials, 2020, 49, 5260-5265.	2.2	3
14	Temperature and DC Bias Dependences of Dielectric Behavior of Different Oriented 0.23PIN-0.52PMN-0.25PT Single Crystals. Journal of Electronic Materials, 2018, 47, 6282-6288.	2.2	2
15	Dislocation evolution along the growth direction of 2-inch GaN crystal grown by Na-flux LPE. Materials Science in Semiconductor Processing, 2021, 126, 105684.	4.0	2
16	Thermal expansion characteristics of [001]-oriented PIN-PMN-PT single crystal. , 2015, , .		1
17	Temperature and DC bias dependence of the phase transition behavior of [011]- and [001]-oriented PIN–PMN–PT single crystals with MPB composition. Journal of Materials Research, 2018, 33, 4053-4061.	2.6	1